

PNP Darlington Transistor BC516

Features

- This Device is Designed for Applications Reguiring Extremely High Current Gain at Currents to 1 A.
- This is a Pb-Free Device

ABSOLUTE MAXIMUM RATINGS

(Values are at T_A = 25°C unless otherwise noted.)

Symbol	Parameter	Value	Unit	
V _{CEO}	Collector-Emitter Voltage	-30	V	
V_{CBO}	Collector-Base Voltage	-40	V	
V _{EBO}	Emitter-Base Voltage	-10	V	
I _C	I _C Collector Current-Continuous		Α	
T_J, T_{STG}	Junction and Storage Junction Temperature Range	-55 to +150	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS (Note1)

(Values are at $T_A = 25$ °C unless otherwise noted.)

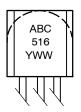
Symbol	Parameter	Max.	Unit	
P_{D}	Total Device Dissipation, T _A = 25°C	625	mW	
$R_{ heta JA}$	Thermal Resistance, Junction-to-Ambient	200	°C/W	
$R_{ heta JC}$	Thermal Resistance, Junction-to-Case	83.3	°C/W	

^{1.} PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

- Collector 1.
- 2. Base
- Emitter

TO-92-3 CASE 135AR

MARKING DIAGRAM



= Assembly Location BC516 = Specific Device Code

= Year WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping [†]
BC516-D27Z	TO-92 3L	2000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (Note 2)

Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур,	Max.	Unit
V_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = -2 \text{ mA}, I_B = 0$	-30	-	-	V
V_{CBO}	Emitter-Base Breakdown Voltage	$I_C = -100 \mu A, I_E = 0$	-40	-	-	V
V_{EBO}	Emitter-Base Breakdown Voltage	$I_E = -10 \mu A, I_C = 0$	-10	-	-	V
I _{CBO}	Collector Cut-Off Current	$V_{CB} = -30 \text{ V}, I_{E} = 0$	_	-	-100	nA
h _{FE}	DC Current Gain	$I_C = -20 \text{ mA}, V_{CE} = -2 \text{ V}$	30,000	-	-	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = -100 \text{ mA}, I_B = -0.1 \text{ mA}$	_	-	-1	V
V _{BE} (on)	Base-Emitter On Voltage	$I_C = -10 \text{ mA}, V_{CE} = -5 \text{ V}$	_	-	-1.4	V
f _T	Current Gain – Bandwidth Product (Note 3)	$I_C = -10 \text{ mA}, V_{CE} = -5 \text{ V},$ f = 100 MHz	-	200	-	MHz

1

^{2.} Pulse Test: Pulse Width ≤ 0. 2%.

^{3.} $f_T = lh_{fe}l \cdot f_{test}$

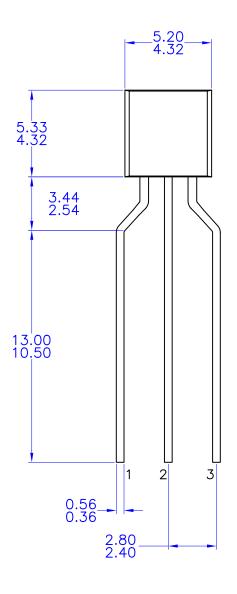


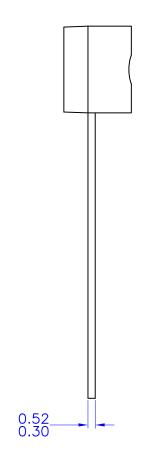


TO-92 3 4.83x4.76 LEADFORMED

CASE 135AR ISSUE O

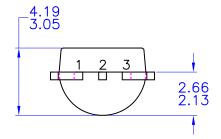
DATE 30 SEP 2016





NOTES: UNLESS OTHERWISE SPECIFIED

- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-1994



DOCUMENT NUMBER:	98AON13879G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	TO-92 3 4 83X4 76 LEADFORMED		PAGE 1 OF 1

onsemi and Onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales